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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

CHO ET AL.

Atty. Ref.: 4105-73; Confirmation No. 6675

Appl. No. 10/568,770

TC/A.U. 1792

Filed: February 21, 2006

Examiner: George

For: FERROELECTRIC THIN-FILM PRODUCTION METHOD, VOLTAGE-APPLICATION
ETCHING APPARATUS, FERROELECTRIC CRYSTAL THIN-FILM SUBSTRATE,
AND FERROELECTRIC CRYSTAL WAFER

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February 13, 2008

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

RESPONSE TO REQUIREMENT FOR RESTRICTION

Responsive to the Official Action of January 25, 2008 and the requirement for restriction presented in it, applicant elects the subject matter of claims 1-20, Group I, directed to a method. This response is made without traverse.

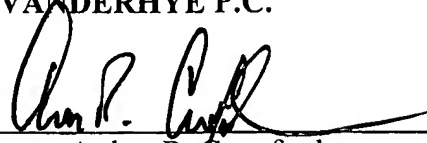
Please examine the elected claims on the merits taking into account the documents cited in the International Search Report in the underlying PCT application and the Information Disclosure Statement filed February 21, 2006.

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Respectfully submitted,

NIXON & VANDERHYE P.C.

By: _____



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